

In the Claims

Please amend Claims 1 and 4 as set forth in the Complete Listing of Claims below:

Complete Listing of Claims

Claim 1 (currently amended): A method for manufacturing a semiconductor device using a plurality of deposited and patterned layers of polysilicon, an oxide sacrificial material, and a metal layer including aluminum comprising the step of etching the oxide sacrificial material by immersing the semiconductor device into an etching solution comprising hydrofluoric acid (HF) and sulfuric acid (H_2SO_4) in a ratio HF: H_2SO_4 ranging from 1:1 to 3:1

Claim 2 (cancelled)

Claim 3 (cancelled)

Claim 4 (currently amended): The method of ~~Claim 3~~ Claim 1 wherein the etching solution has an etch selectivity for the oxide sacrificial material relative to the metal layer of greater than 100.

Claim 5 (original): The method of Claim 1 wherein the semiconductor device comprises a micromechanical device, a microelectromechanical device or a microfluidic device.

Claim 6 (original): The method of Claim 1 wherein the step of etching the oxide sacrificial material is performed with the etching solution at a temperature in the range of 5 - 70 °C.

Claim 7 (original): The method of Claim 1 wherein the hydrofluoric acid comprises a "semiconductor grade" hydrofluoric acid, and the sulfuric acid comprises a "semiconductor grade" sulfuric acid.

Claim 8 (original): The method of Claim 1 wherein the hydrofluoric acid comprises at least 40 - 50% by weight HF.

Claim 9 (original): The method of Claim 1 wherein the sulfuric acid comprises at least 90% by weight H_2SO_4 .

PATENT

Serial No.: 10/ 010,850

Group No.: 1765

Page 3

Claim 10 (cancelled)

Claims 11 - 18 (cancelled)